PSMN015-100P

N-channel TrenchMOS SiliconMAX standard level FET

Rev. 06 — 17 December 2009 Product data sheet

1. Product profile

1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Rated for avalanche ruggedness

1.3 Applications

- DC-to-DC convertors
- Switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	-	100	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; see Figure 1 and 3	-	-	75	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2	-	-	300	W
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10$ V; $I_D = 75$ A; $V_{DS} = 80$ V; $T_j = 25$ °C; see Figure 11	-	35	-	nC
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 25$ °C; see Figure 9 and 10	-	12	15	mΩ

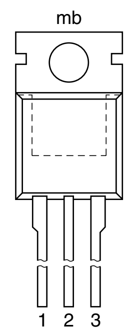
founded by Philips

2. Pinning information

Table 2. Pinning information

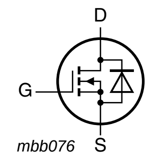
Pin	Symbol	Description
1	G	gate
2	D	drain
3	S	source
mb	D	mounting base; connected to drain

Simplified outline



SOT78 (TO-220AB)

Graphic symbol



3. Ordering information

Table 3. Ordering information

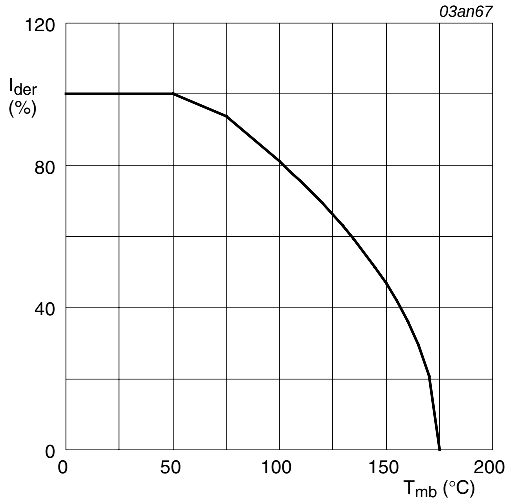
Type number	Package		
	Name	Description	Version
PSMN015-100P	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

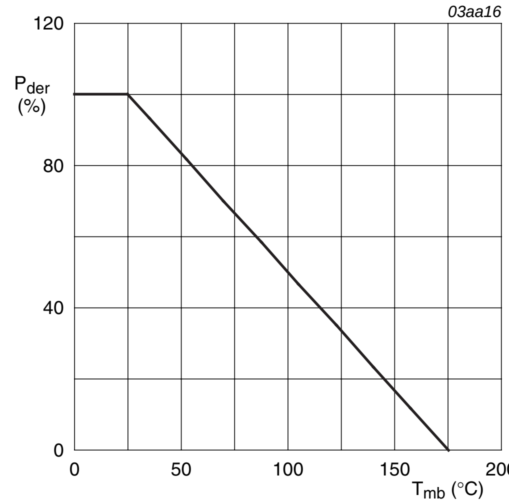
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	100	V
V_{DGR}	drain-gate voltage	$T_j \leq 175$ °C; $T_j \geq 25$ °C; $R_{GS} = 20$ kΩ	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10$ V; $T_{mb} = 100$ °C; see Figure 1	-	60.8	A
		$V_{GS} = 10$ V; $T_{mb} = 25$ °C; see Figure 1 and 3	-	75	A
I_{DM}	peak drain current	$t_p \leq 10$ µs; pulsed; $T_{mb} = 25$ °C; see Figure 3	-	240	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2	-	300	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25$ °C	-	75	A
I_{SM}	peak source current	$t_p \leq 10$ µs; pulsed; $T_{mb} = 25$ °C	-	240	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 36$ A; $V_{sup} \leq 50$ V; unclamped; $t_p = 0.11$ ms; $R_{GS} = 50$ Ω	-	320	mJ



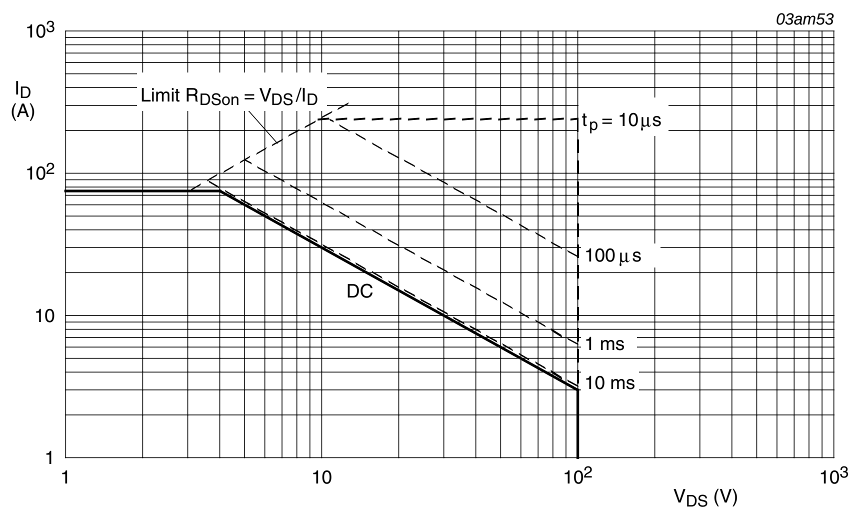
$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\,\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25°C; I_{DM}$ is single pulse; $V_{GS} = 10V$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

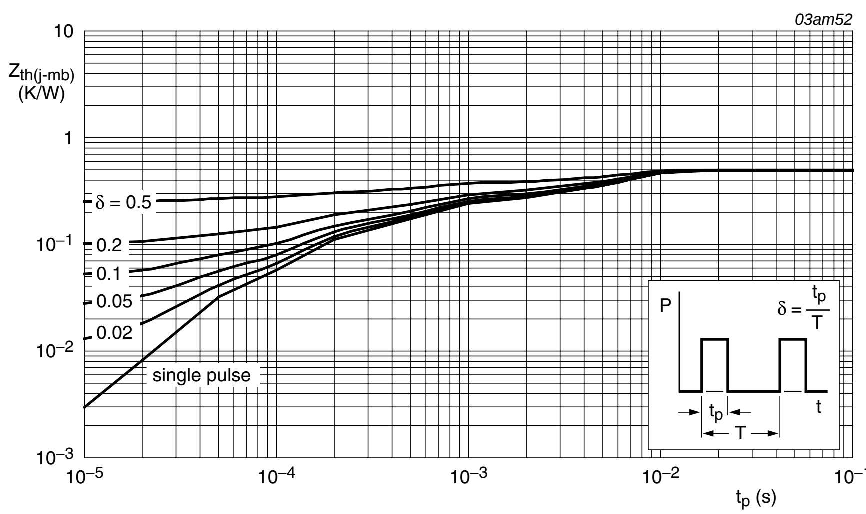
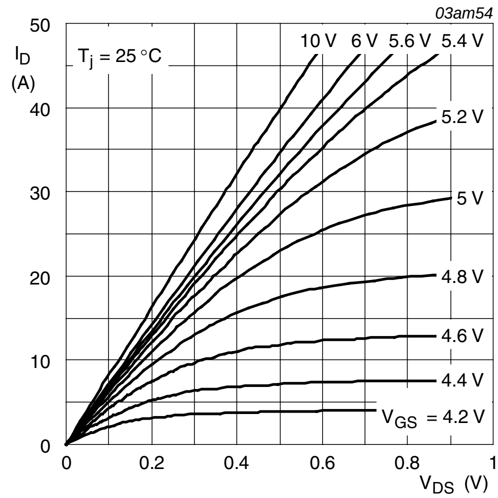


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

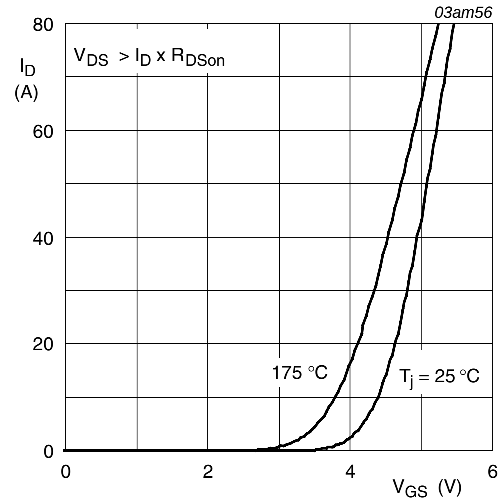
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	89	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS}= V_{GS}; T_j = 175 °C; see Figure 8	1	-	-	V
		I_D = 1 mA; V_{DS}= V_{GS}; T_j = -55 °C; see Figure 8	-	-	4.4	V
		I_D = 1 mA; V_{DS}= V_{GS}; T_j = 25 °C; see Figure 8	2	3	4	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	µA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C; see Figure 9	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C; see Figure 9	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 9 and 10	-	32.4	40.5	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 9 and 10	-	12	15	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 75 A; V_{DS} = 80 V; V_{GS} = 10 V; T_j = 25 °C; see Figure 11	-	90	-	nC
Q_{GS}	gate-source charge	I_D = 75 A; V_{DS} = 80 V; V_{GS} = 10 V; see Figure 11	-	20	-	nC
Q_{GD}	gate-drain charge	I_D = 75 A; V_{DS} = 80 V; V_{GS} = 10 V; T_j = 25 °C; see Figure 11	-	35	-	nC
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 12	-	4900	-	pF
C_{oss}	output capacitance		-	390	-	pF
C_{rss}	reverse transfer capacitance		-	220	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 50 V; R_L = 1.8 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5.6 Ω; T_j = 25 °C	-	25	-	ns
t_r	rise time		-	65	-	ns
$t_{d(off)}$	turn-off delay time		-	95	-	ns
t_f	fall time		-	50	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 13	-	0.8	1.1	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C	-	80	-	ns
Q_r	recovered charge		-	115	-	nC



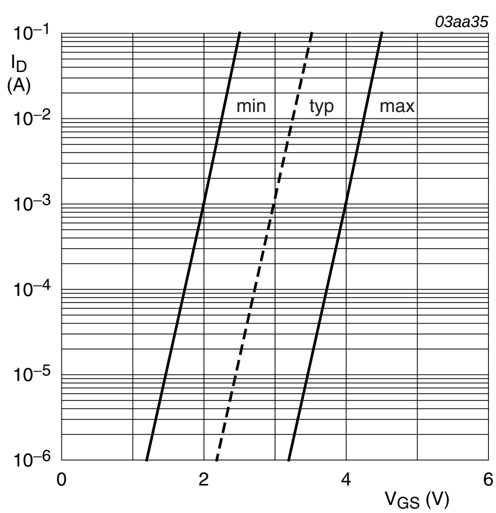
$T_j = 25°C$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



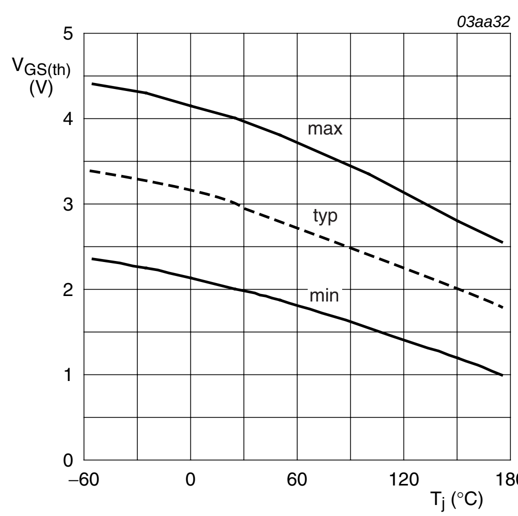
$T_j = 25°C$ and $175°C$; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



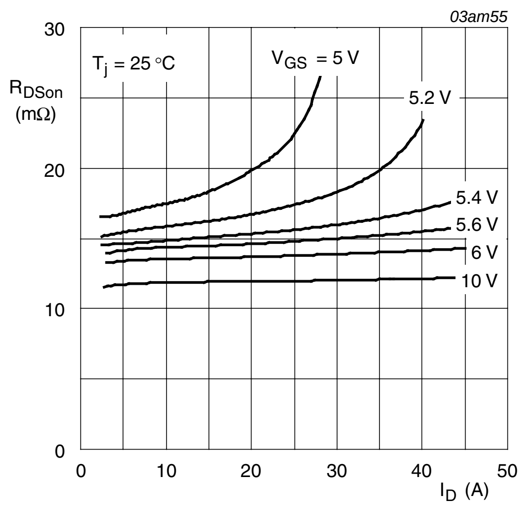
$T_j = 25\,°C; V_{DS} = 5V$

Fig 7. Sub-threshold drain current as a function of gate-source voltage



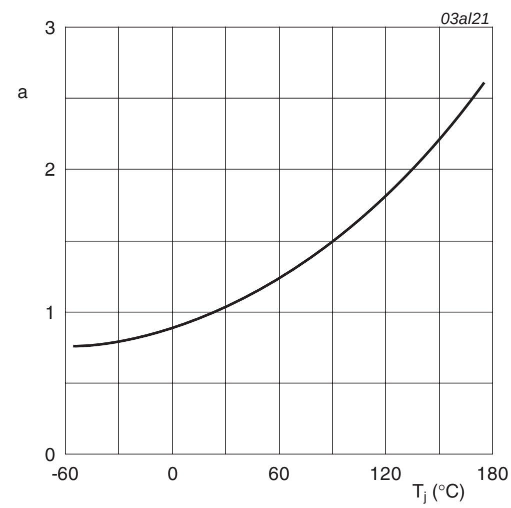
$I_D = 1mA; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature



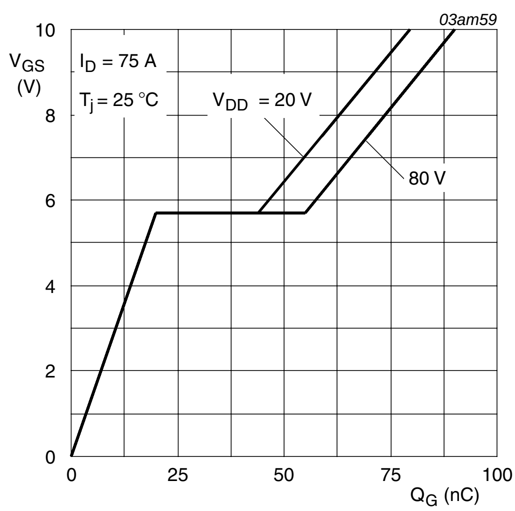
$$T_j = 25°C$$

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



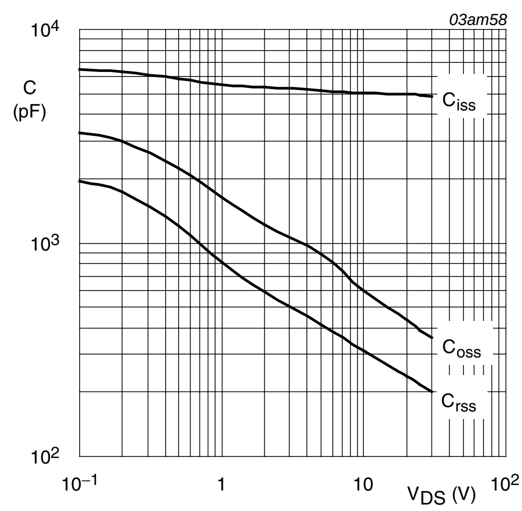
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



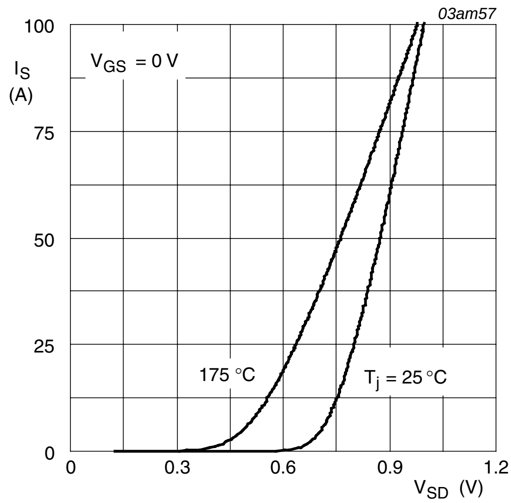
$$I_D = 75\ A;\ T_j = 25\ °C$$

Fig 11. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0V;\ f = 1MHz$$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

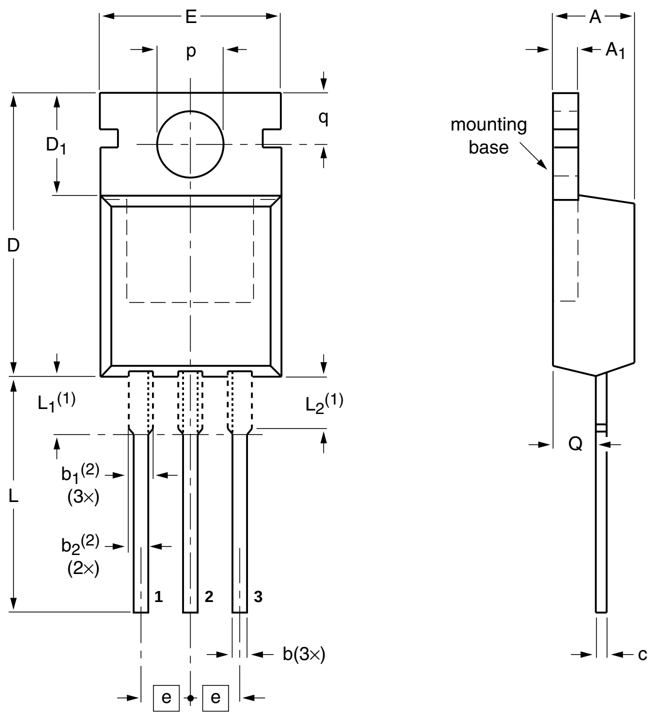


$T_j = 25°C$ and $175°C; V_{GS} = 0V$

Fig 13. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	$b_1^{(2)}$	$b_2^{(2)}$	c	D	D_1	E	e	L	$L_1^{(1)}$	$L_2^{(1)}$ max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

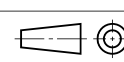
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Fig 14. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN015-100P_6	20091217	Product data sheet	-	PSMN015_100P_100B-05
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Type number PSMN015-100P separated from data sheet PSMN015_100P_100B-05.			
PSMN015_100P_100B-05	20040114	Product data	-	PSMN015-100_SERIES_4
PSMN015-100_SERIES_4	20030601	Product specification	-	PSMN015-100_SERIES_HG_3
PSMN015-100_SERIES_HG_3	20000328	Product specification	-	PSMN015-100_SERIES_2
PSMN015-100_SERIES_2	19990801	Product specification	-	PSMN015-100_SERIES_1
PSMN015-100_SERIES_1	19990201	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URLhttp://www.nxp.com.

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10. Contact information

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For sales office addresses, please send an email to:salesaddresses@nxp.com

11. Contents

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